

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

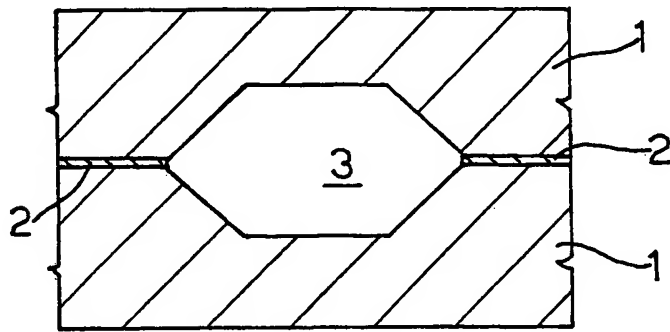


FIG. 1
(Prior Art)

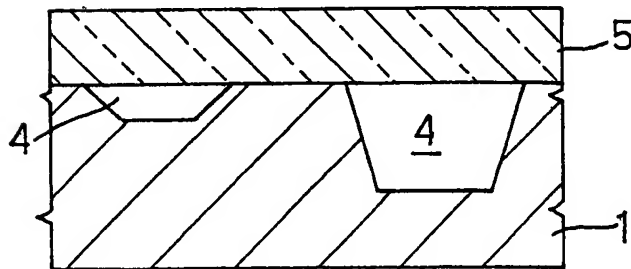


FIG. 2
(Prior Art)

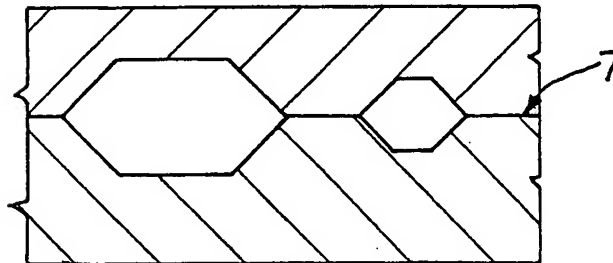


FIG. 3
(Prior Art)

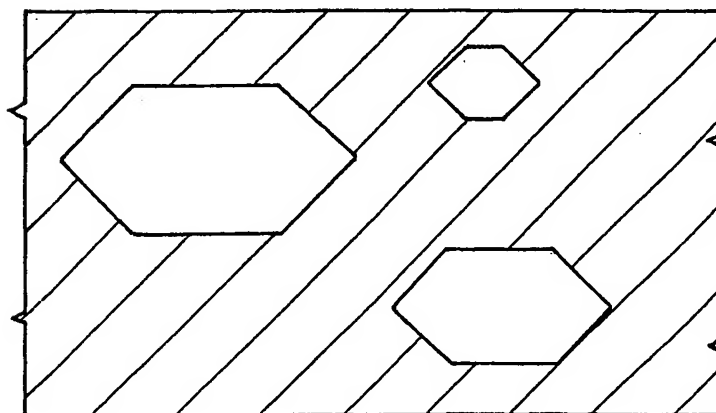


FIG. 4

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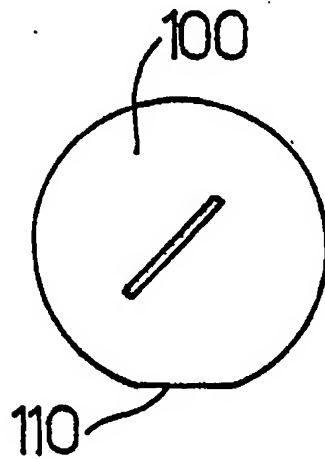


FIG. 5

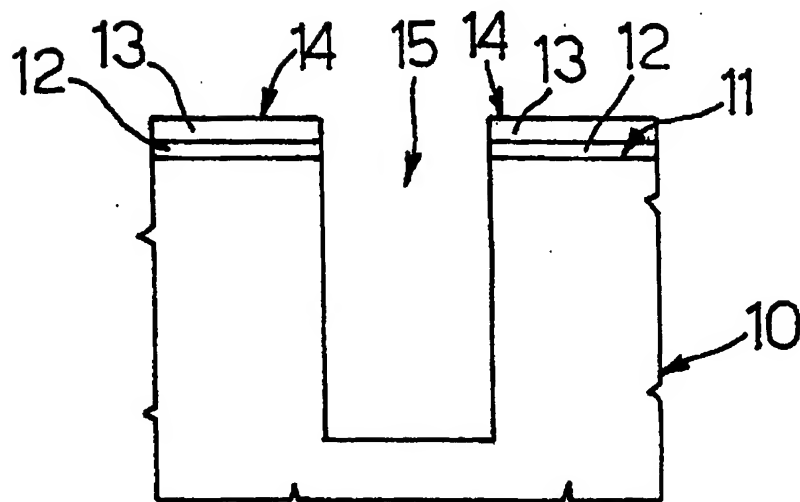


FIG. 6

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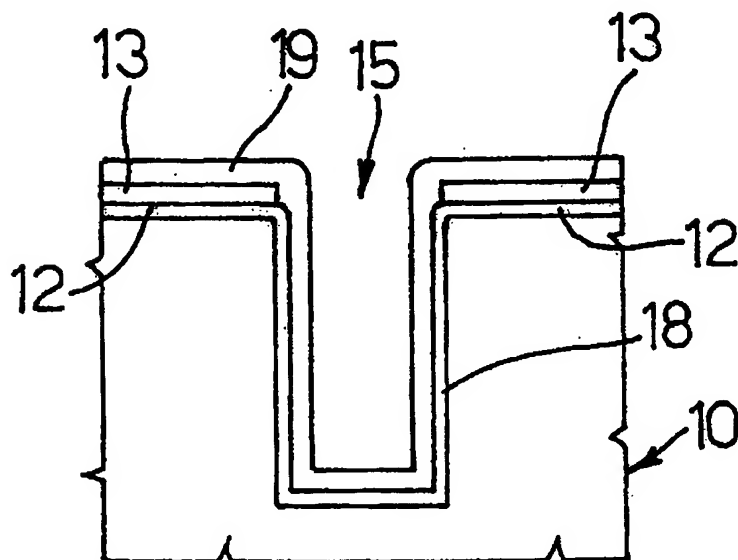


FIG. 7

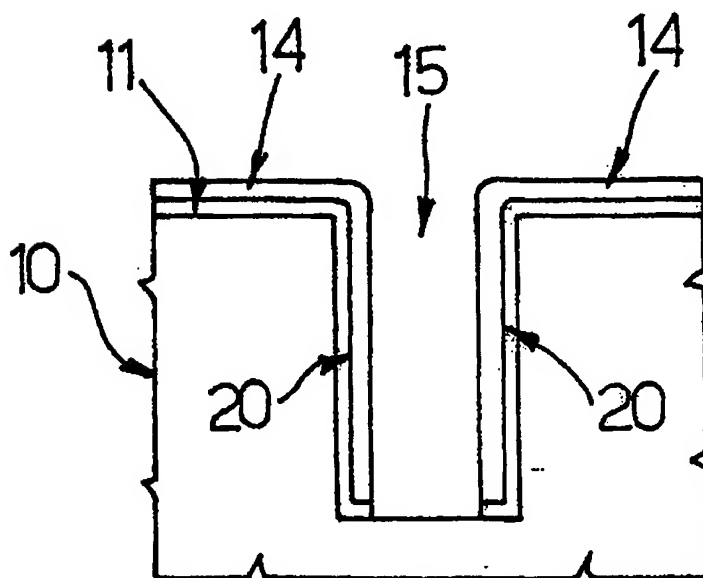


FIG. 8

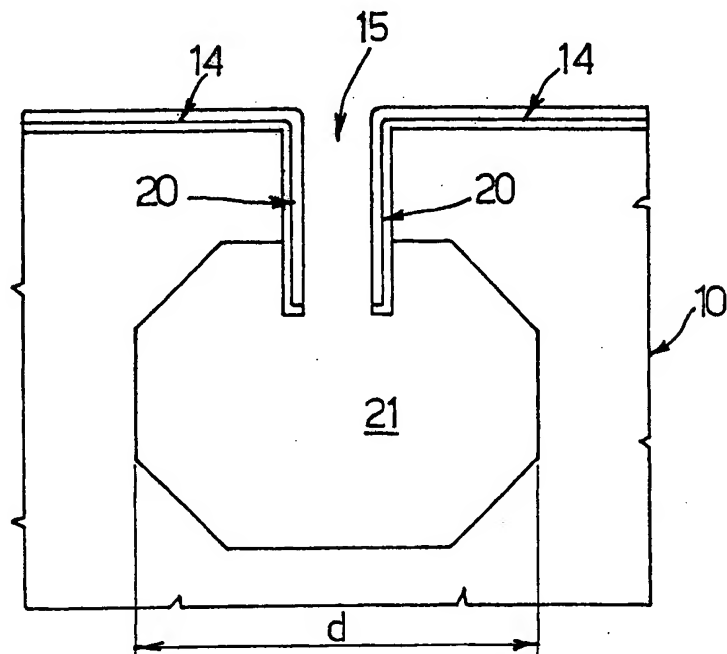


FIG. 9

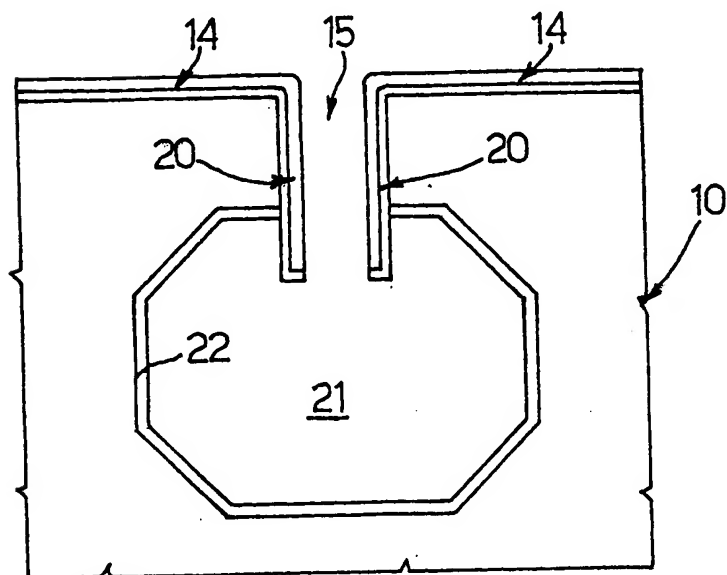


FIG. 10

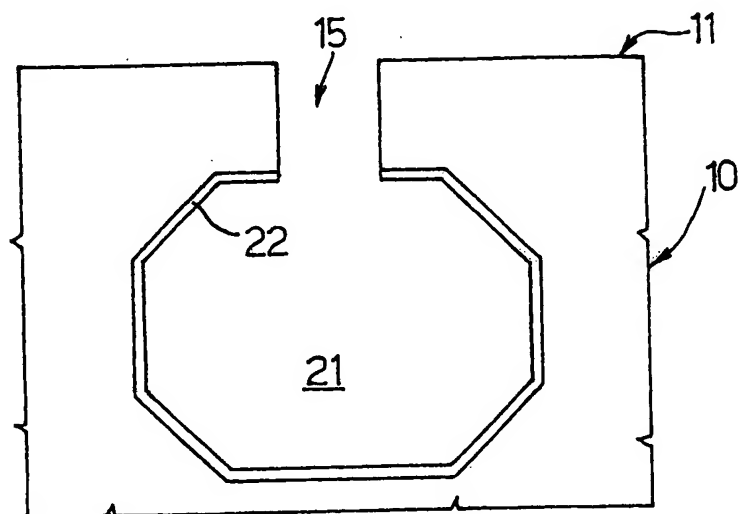


FIG. 11

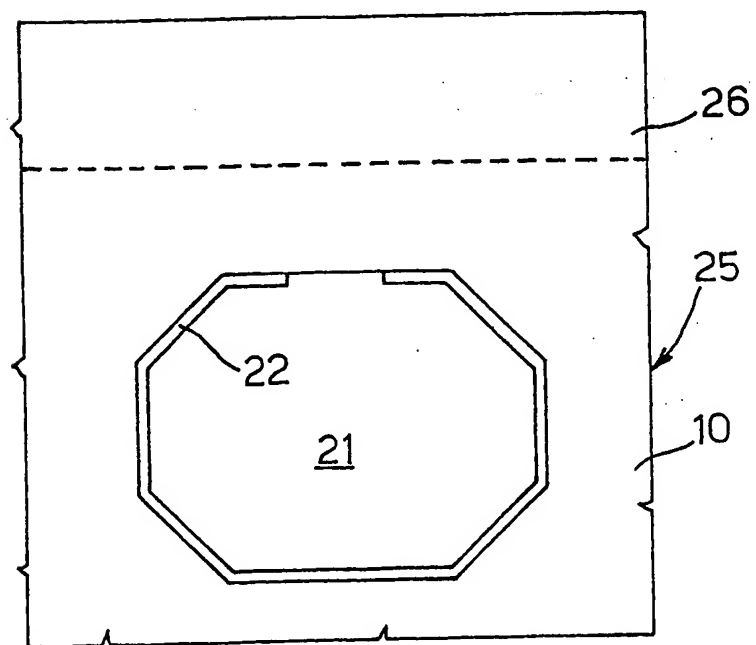


FIG. 12

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FIG. 13

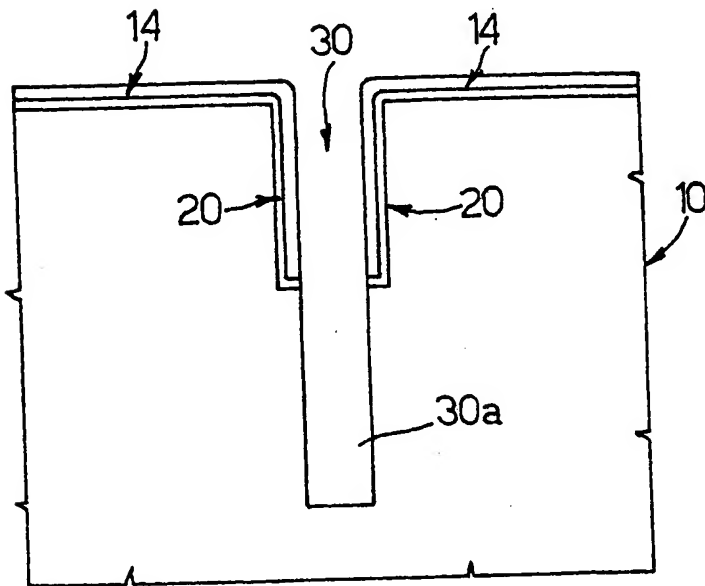
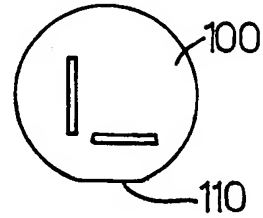


FIG. 14

FIG. 15

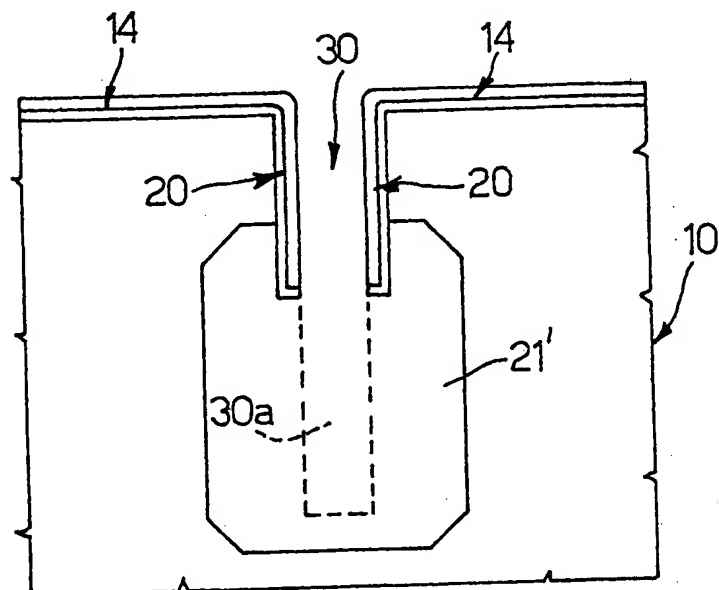


FIG. 16

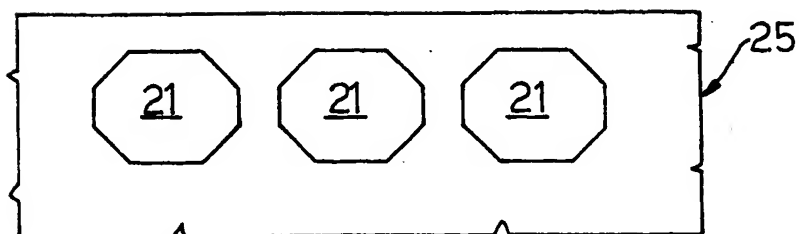
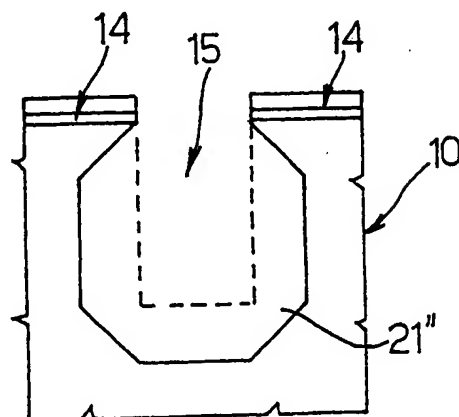


FIG. 17

FIG. 18

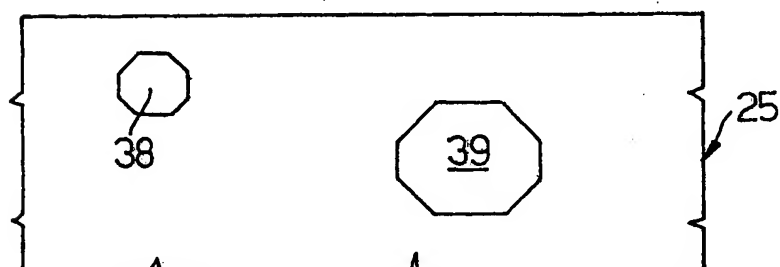
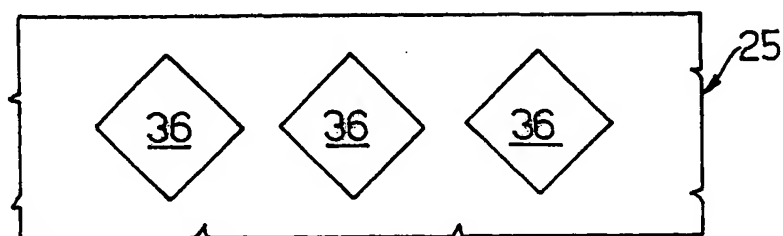


FIG. 19

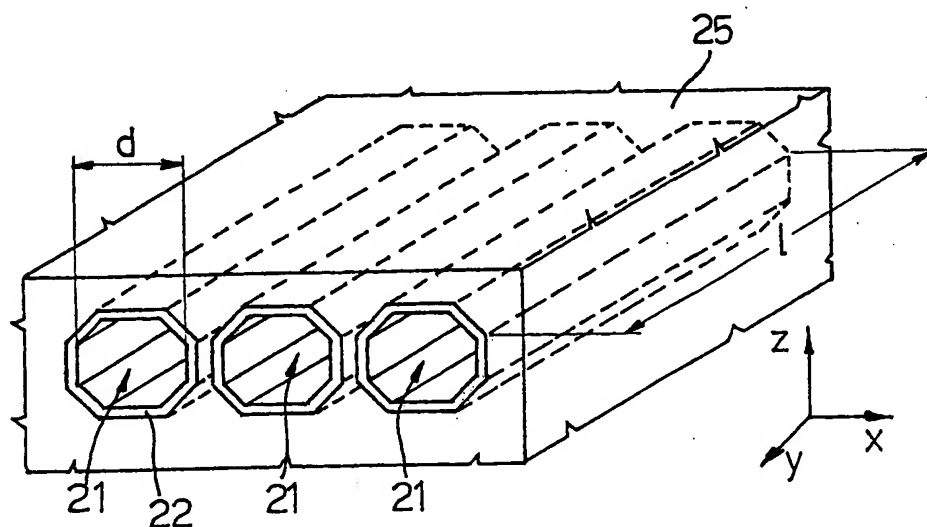


FIG. 20

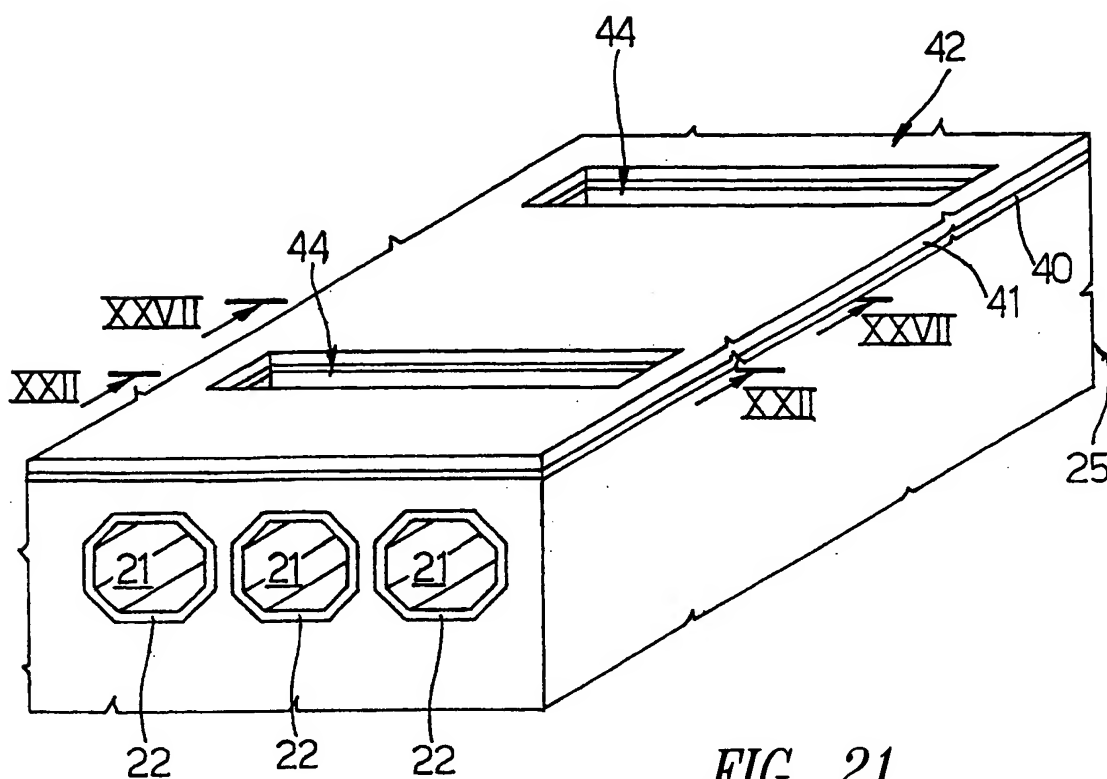


FIG. 21

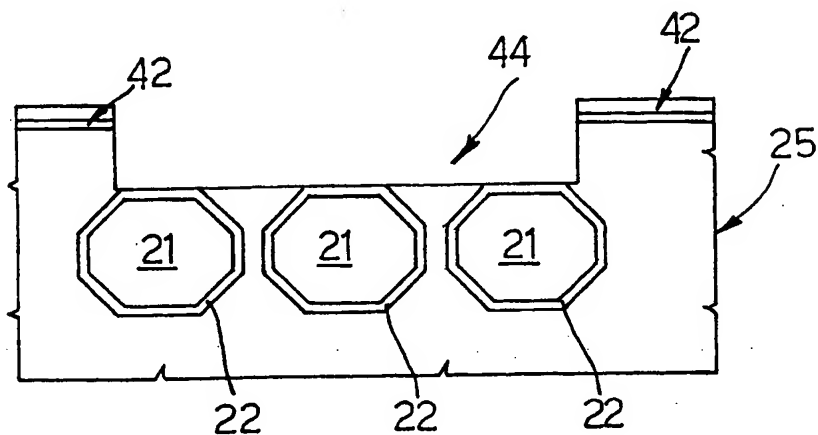


FIG. 22

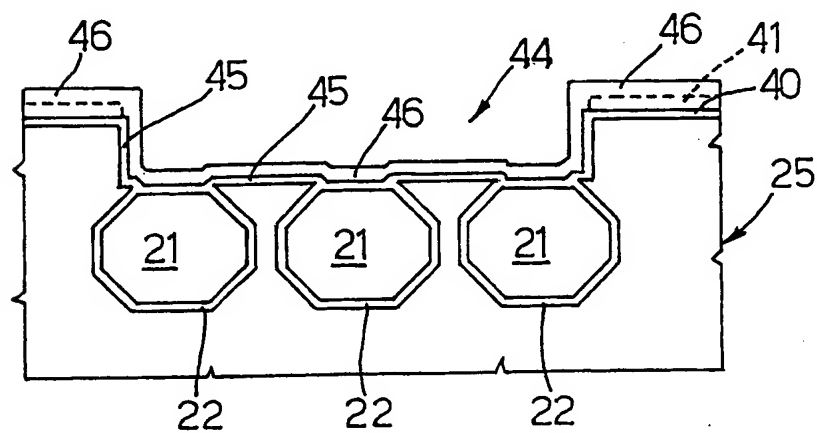


FIG. 23

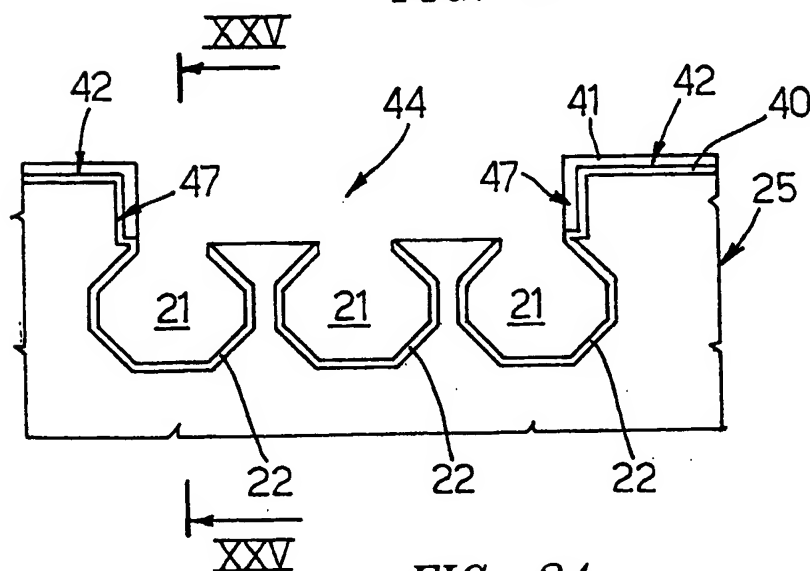


FIG. 24

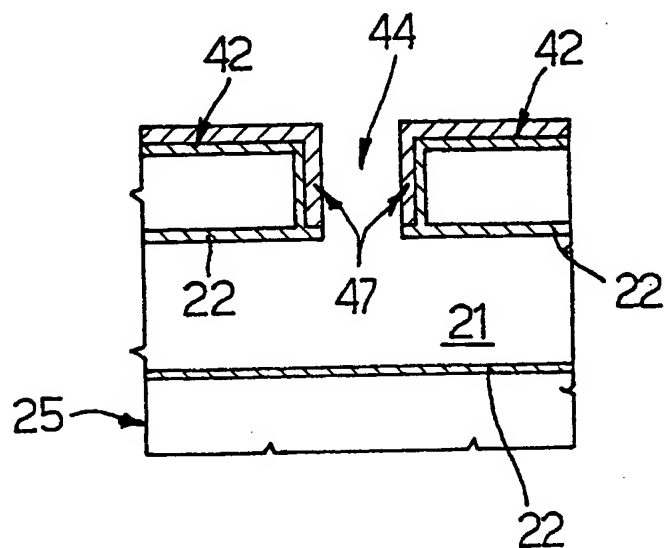


FIG. 25

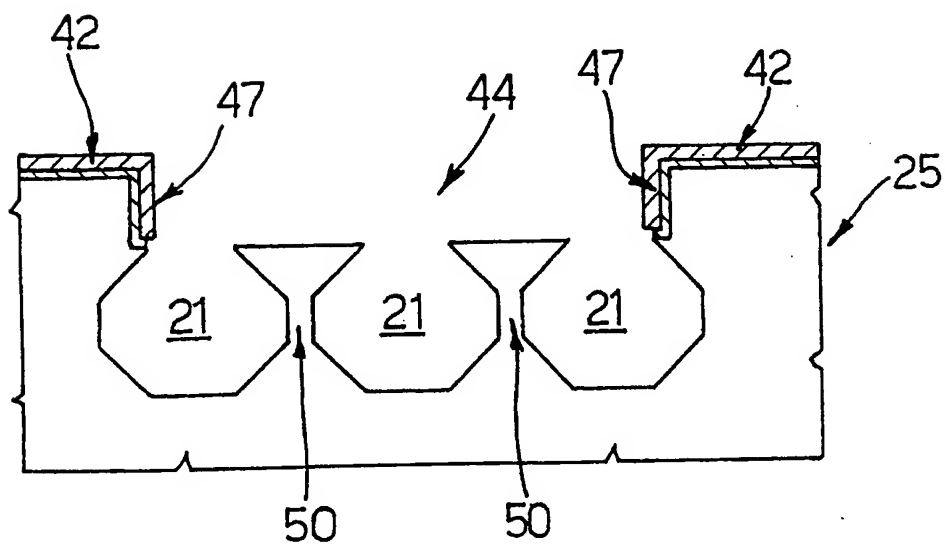


FIG. 26

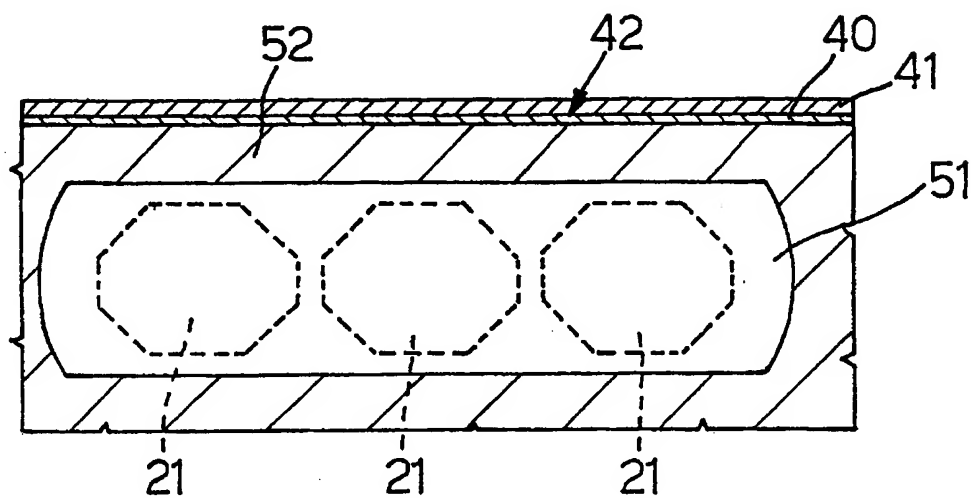


FIG. 27

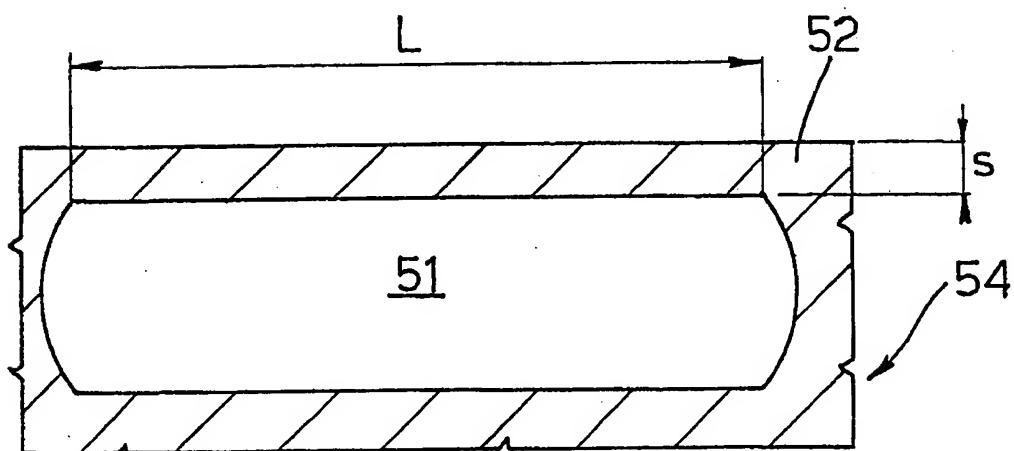


FIG. 28